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Understanding Embedded - Microprocessors

Embedded microprocessors are specialized computing chips designed to perform specific tasks within an embedded system. Unlike general-purpose microprocessors found in personal computers, embedded microprocessors are tailored for dedicated functions within larger systems, offering optimized performance, efficiency, and reliability. These microprocessors are integral to the operation of countless electronic devices, providing the computational power necessary for controlling processes, handling data, and managing communications.

Applications of Embedded - Microprocessors

Embedded microprocessors are utilized across a broad spectrum of applications, making them indispensable in

Details	
Product Status	Active
Core Processor	PowerPC e500mc
Number of Cores/Bus Width	4 Core, 32-Bit
Speed	667MHz
Co-Processors/DSP	-
RAM Controllers	DDR3, DDR3L
Graphics Acceleration	No
Display & Interface Controllers	-
Ethernet	10/100/1000Mbps (5)
SATA	SATA 3Gbps (2)
USB	USB 2.0 + PHY (2)
Voltage - I/O	1.0V, 1.35V, 1.5V, 1.8V, 2.5V, 3.3V
Operating Temperature	0°C ~ 105°C (TA)
Security Features	-
Package / Case	-
Supplier Device Package	780-FCPBGA (23x23)
Purchase URL	https://www.e-xfl.com/pro/item?MUrl=&PartUrl=p2040nsn7flc

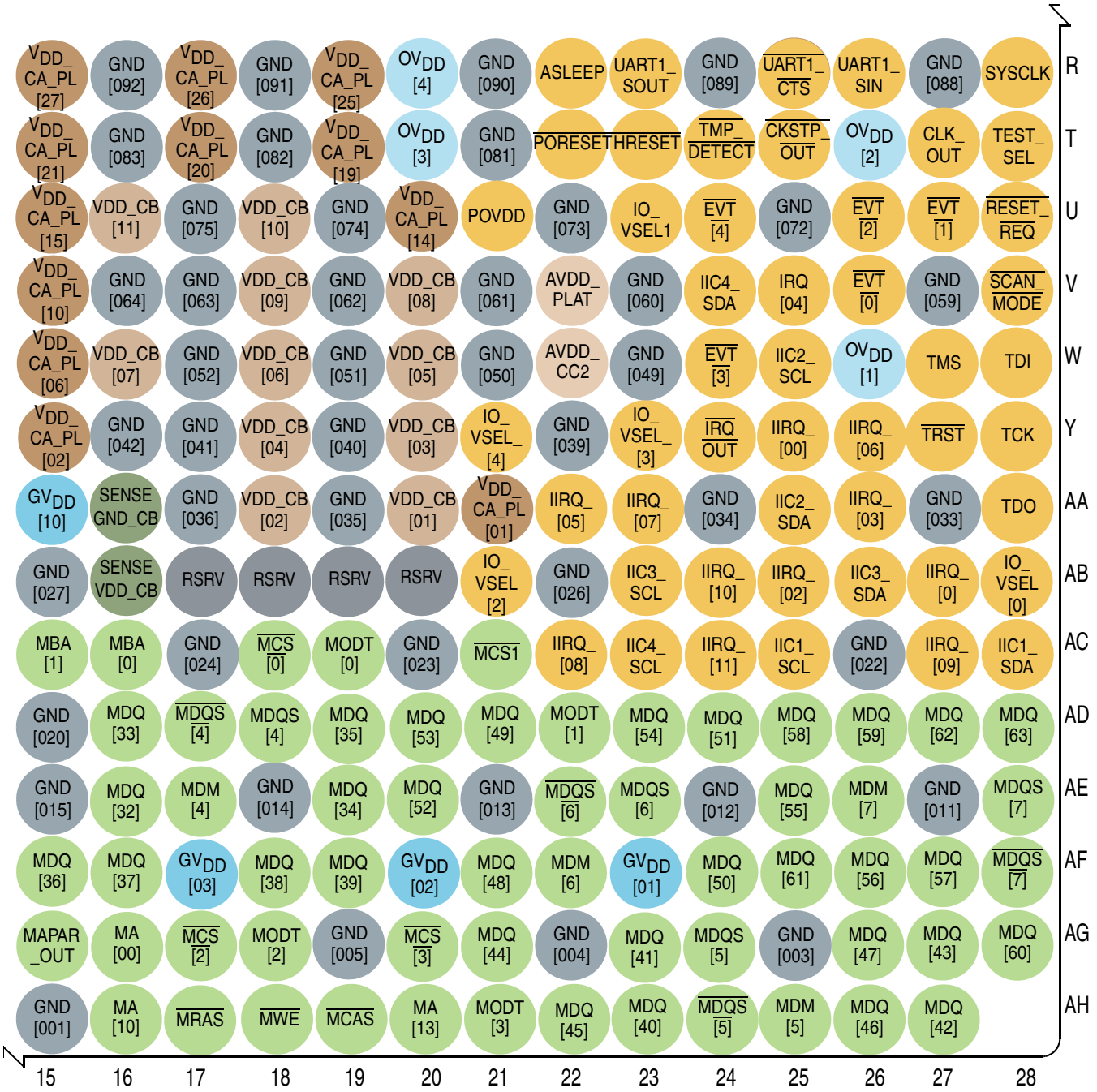


Figure 6. 780 BGA Ball Map Diagram (Detail View D)

Table 1. Pin List by Bus (continued)

Signal	Signal Description	Package Pin Number	Pin Type	Power Supply	Note
$\overline{\text{MDQS5}}$	Data Strobe	AH24	I/O	GV_{DD}	—
$\overline{\text{MDQS6}}$	Data Strobe	AE22	I/O	GV_{DD}	—
$\overline{\text{MDQS7}}$	Data Strobe	AF28	I/O	GV_{DD}	—
$\overline{\text{MDQS8}}$	Data Strobe	AG3	I/O	GV_{DD}	—
MBA0	Bank Select	AC16	O	GV_{DD}	—
MBA1	Bank Select	AC15	O	GV_{DD}	—
MBA2	Bank Select	AC8	O	GV_{DD}	—
MA00	Address	AG16	O	GV_{DD}	—
MA01	Address	AF12	O	GV_{DD}	—
MA02	Address	AC12	O	GV_{DD}	—
MA03	Address	AH11	O	GV_{DD}	—
MA04	Address	AG11	O	GV_{DD}	—
MA05	Address	AH10	O	GV_{DD}	—
MA06	Address	AC11	O	GV_{DD}	—
MA07	Address	AC10	O	GV_{DD}	—
MA08	Address	AF10	O	GV_{DD}	—
MA09	Address	AH9	O	GV_{DD}	—
MA10	Address	AH16	O	GV_{DD}	—
MA11	Address	AG9	O	GV_{DD}	—
MA12	Address	AC9	O	GV_{DD}	—
MA13	Address	AH20	O	GV_{DD}	—
MA14	Address	AG8	O	GV_{DD}	—
MA15	Address	AH7	O	GV_{DD}	—
$\overline{\text{MWE}}$	Write Enable	AH18	O	GV_{DD}	—
$\overline{\text{MRAS}}$	Row Address Strobe	AH17	O	GV_{DD}	—
$\overline{\text{MCAS}}$	Column Address Strobe	AH19	O	GV_{DD}	—
$\overline{\text{MCS0}}$	Chip Select	AC18	O	GV_{DD}	—
$\overline{\text{MCS1}}$	Chip Select	AC21	O	GV_{DD}	—
$\overline{\text{MCS2}}$	Chip Select	AG17	O	GV_{DD}	—
$\overline{\text{MCS3}}$	Chip Select	AG20	O	GV_{DD}	—
MCKE0	Clock Enable	AB8	O	GV_{DD}	—
MCKE1	Clock Enable	AB7	O	GV_{DD}	—
MCKE2	Clock Enable	AH6	O	GV_{DD}	—
MCKE3	Clock Enable	AG6	O	GV_{DD}	—

Table 1. Pin List by Bus (continued)

Signal	Signal Description	Package Pin Number	Pin Type	Power Supply	Note
MCK0	Clock	AD14	O	GV_{DD}	—
MCK1	Clock	AE13	O	GV_{DD}	—
MCK2	Clock	AG13	O	GV_{DD}	—
MCK3	Clock	AG14	O	GV_{DD}	—
$\overline{\text{MCK0}}$	Clock Complements	AE14	O	GV_{DD}	—
$\overline{\text{MCK1}}$	Clock Complements	AD13	O	GV_{DD}	—
$\overline{\text{MCK2}}$	Clock Complements	AH13	O	GV_{DD}	—
$\overline{\text{MCK3}}$	Clock Complements	AH14	O	GV_{DD}	—
MODT0	On Die Termination	AC19	O	GV_{DD}	—
MODT1	On Die Termination	AD22	O	GV_{DD}	—
MODT2	On Die Termination	AG18	O	GV_{DD}	—
MODT3	On Die Termination	AH21	O	GV_{DD}	—
MDIC0	Driver Impedance Calibration	AG12	I/O	GV_{DD}	16
MDIC1	Driver Impedance Calibration	AE12	I/O	GV_{DD}	16
Local Bus Controller Interface					
LAD00	Muxed Data/Address	J6	I/O	BV_{DD}	3
LAD01	Muxed Data/Address	J4	I/O	BV_{DD}	3
LAD02	Muxed Data/Address	K2	I/O	BV_{DD}	3
LAD03	Muxed Data/Address	K4	I/O	BV_{DD}	3
LAD04	Muxed Data/Address	L1	I/O	BV_{DD}	3
LAD05	Muxed Data/Address	J5	I/O	BV_{DD}	3
LAD06	Muxed Data/Address	N5	I/O	BV_{DD}	3
LAD07	Muxed Data/Address	N2	I/O	BV_{DD}	3
LAD08	Muxed Data/Address	N3	I/O	BV_{DD}	3
LAD09	Muxed Data/Address	N1	I/O	BV_{DD}	3
LAD10	Muxed Data/Address	P4	I/O	BV_{DD}	3
LAD11	Muxed Data/Address	R7	I/O	BV_{DD}	3
LAD12	Muxed Data/Address	T4	I/O	BV_{DD}	3
LAD13	Muxed Data/Address	U2	I/O	BV_{DD}	3
LAD14	Muxed Data/Address	T6	I/O	BV_{DD}	3
LAD15	Muxed Data/Address	T7	I/O	BV_{DD}	3
LA16	Address	K6	I/O	BV_{DD}	31
LA17	Address	K3	I/O	BV_{DD}	31
LA18	Address	P6	I/O	BV_{DD}	31

Table 1. Pin List by Bus (continued)

Signal	Signal Description	Package Pin Number	Pin Type	Power Supply	Note
GND064	Ground	V16	—	—	—
GND063	Ground	V17	—	—	—
GND062	Ground	V19	—	—	—
GND061	Ground	V21	—	—	—
GND060	Ground	V23	—	—	—
GND059	Ground	V27	—	—	—
GND058	Ground	W2	—	—	—
GND057	Ground	W5	—	—	—
GND056	Ground	W8	—	—	—
GND055	Ground	W10	—	—	—
GND054	Ground	W12	—	—	—
GND053	Ground	W14	—	—	—
GND052	Ground	W17	—	—	—
GND051	Ground	W19	—	—	—
GND050	Ground	W21	—	—	—
GND049	Ground	W23	—	—	—
GND048	Ground	Y6	—	—	—
GND047	Ground	Y7	—	—	—
GND046	Ground	Y8	—	—	—
GND045	Ground	Y10	—	—	—
GND044	Ground	Y12	—	—	—
GND043	Ground	Y14	—	—	—
GND042	Ground	Y16	—	—	—
GND041	Ground	Y17	—	—	—
GND040	Ground	Y19	—	—	—
GND039	Ground	Y22	—	—	—
GND038	Ground	AA5	—	—	—
GND037	Ground	AA7	—	—	—
GND036	Ground	AA17	—	—	—
GND035	Ground	AA19	—	—	—
GND034	Ground	AA24	—	—	—
GND033	Ground	AA27	—	—	—
GND032	Ground	AB2	—	—	—
GND031	Ground	AB9	—	—	—

Table 1. Pin List by Bus (continued)

Signal	Signal Description	Package Pin Number	Pin Type	Power Supply	Note
VDD_CA_PL50	Core Group A and Platform Supply	L17	—	$V_{DD\_CA\_PL}$	37
VDD_CA_PL49	Core Group A and Platform Supply	L19	—	$V_{DD\_CA\_PL}$	37
VDD_CA_PL48	Core Group A and Platform Supply	M9	—	$V_{DD\_CA\_PL}$	37
VDD_CA_PL47	Core Group A and Platform Supply	M11	—	$V_{DD\_CA\_PL}$	37
VDD_CA_PL46	Core Group A and Platform Supply	M13	—	$V_{DD\_CA\_PL}$	37
VDD_CA_PL45	Core Group A and Platform Supply	M15	—	$V_{DD\_CA\_PL}$	37
VDD_CA_PL44	Core Group A and Platform Supply	M17	—	$V_{DD\_CA\_PL}$	37
VDD_CA_PL43	Core Group A and Platform Supply	M19	—	$V_{DD\_CA\_PL}$	37
VDD_CA_PL42	Core Group A and Platform Supply	N9	—	$V_{DD\_CA\_PL}$	37
VDD_CA_PL41	Core Group A and Platform Supply	N11	—	$V_{DD\_CA\_PL}$	37
VDD_CA_PL40	Core Group A and Platform Supply	N13	—	$V_{DD\_CA\_PL}$	37
VDD_CA_PL39	Core Group A and Platform Supply	N15	—	$V_{DD\_CA\_PL}$	37
VDD_CA_PL38	Core Group A and Platform Supply	N17	—	$V_{DD\_CA\_PL}$	37
VDD_CA_PL37	Core Group A and Platform Supply	N19	—	$V_{DD\_CA\_PL}$	37
VDD_CA_PL36	Core Group A and Platform Supply	P9	—	$V_{DD\_CA\_PL}$	37
VDD_CA_PL35	Core Group A and Platform Supply	P11	—	$V_{DD\_CA\_PL}$	37
VDD_CA_PL34	Core Group A and Platform Supply	P13	—	$V_{DD\_CA\_PL}$	37
VDD_CA_PL33	Core Group A and Platform Supply	P15	—	$V_{DD\_CA\_PL}$	37
VDD_CA_PL32	Core Group A and Platform Supply	P17	—	$V_{DD\_CA\_PL}$	37
VDD_CA_PL31	Core Group A and Platform Supply	P19	—	$V_{DD\_CA\_PL}$	37
VDD_CA_PL30	Core Group A and Platform Supply	R9	—	$V_{DD\_CA\_PL}$	37
VDD_CA_PL29	Core Group A and Platform Supply	R11	—	$V_{DD\_CA\_PL}$	37
VDD_CA_PL28	Core Group A and Platform Supply	R13	—	$V_{DD\_CA\_PL}$	37
VDD_CA_PL27	Core Group A and Platform Supply	R15	—	$V_{DD\_CA\_PL}$	37
VDD_CA_PL26	Core Group A and Platform Supply	R17	—	$V_{DD\_CA\_PL}$	37
VDD_CA_PL25	Core Group A and Platform Supply	R19	—	$V_{DD\_CA\_PL}$	37
VDD_CA_PL24	Core Group A and Platform Supply	T9	—	$V_{DD\_CA\_PL}$	37
VDD_CA_PL23	Core Group A and Platform Supply	T11	—	$V_{DD\_CA\_PL}$	37
VDD_CA_PL22	Core Group A and Platform Supply	T13	—	$V_{DD\_CA\_PL}$	37
VDD_CA_PL21	Core Group A and Platform Supply	T15	—	$V_{DD\_CA\_PL}$	37
VDD_CA_PL20	Core Group A and Platform Supply	T17	—	$V_{DD\_CA\_PL}$	37
VDD_CA_PL19	Core Group A and Platform Supply	T19	—	$V_{DD\_CA\_PL}$	37
VDD_CA_PL18	Core Group A and Platform Supply	U9	—	$V_{DD\_CA\_PL}$	37
VDD_CA_PL17	Core Group A and Platform Supply	U11	—	$V_{DD\_CA\_PL}$	37

Table 7. P2040 I/O Power Supply Estimated Values (continued)

IEEE 1588	—	LVdd (2.5V)	0.004	0.005	W	1,3,6
eLBC	32-bit, 100Mhz	BVdd (1.8V)	0.048	0.120	W	1,3,6
		BVdd (2.5V)	0.072	0.193		
		BVdd (3.3V)	0.120	0.277		
	16-bit, 100Mhz	BVdd (1.8V)	0.021	0.030	W	1,3,6
		BVdd (2.5V)	0.036	0.046		
		BVdd (3.3V)	0.057	0.076		
eSDHC	—	Ovdd (3.3V)	0.014	0.150	W	1,3,6
eSPI	—	CVdd (1.8V)	0.004	0.005	W	1,3,6
		CVdd (2.5V)	0.006	0.008		
		CVdd (3.3V)	0.010	0.013		
USB	—	USB_Vdd_3P3	0.012	0.015	W	1,3,6
I2C	—	OVdd (3.3V)	0.002	0.003	W	1,3,6
DUART	—	OVdd (3.3V)	0.006	0.008	W	1,3,6
GPIO	x8	OVdd (1.8V)	0.005	0.006	W	1,3,4,6
		OVdd (2.5V)	0.007	0.009		
		OVdd (3.3V)	0.009	0.011		
Others (Reset, System Clock, JTAG & Misc)	—	OVdd (3.3V)	0.003	0.015	W	1,3,4,6

Note:

1. The typical values are estimates and based on simulations at 65 °C.
2. Typical DDR power numbers are based on one 2-rank DIMM with 40% utilization.
3. Assuming 15 pF total capacitance load.
4. GPIO's are supported on 1.8 V, 2.5 V and 3.3 V rails as specified in the hardware specification.
5. Maximum DDR power numbers are based on one 2-rank DIMM with 100% utilization.
6. The maximum values are estimated and they are based on simulations at 105 °C. The values are not intended to be used as the maximum guranteed current.
7. The total power numbers of XVDD is dependent on customer application use case. This table lists all the SerDes configuration combination possible for the device. To get the XVDD power numbers, the user should add the combined lanes to match to the total SerDes lanes used, not simply multiply the power numbers by the number of lanes.

Table 21. DDR3L SDRAM Interface DC Electrical Characteristics (GV_{DD} = 1.35 V) (continued)

For recommended operating conditions, see Table 3.

Parameter	Symbol	Min	Max	Unit	Note

Note:

1. GV_{DD} is expected to be within 50 mV of the DRAM's voltage supply at all times. The DRAM's and memory controller's voltage supply may or may not be from the same source.
2. $MV_{REF}n$ is expected to be equal to 0.5 × GV_{DD} and to track GV_{DD} DC variations as measured at the receiver. Peak-to-peak noise on $MV_{REF}n$ may not exceed the $MV_{REF}n$ DC level by more than ±1% of the DC value (that is, ±13.5 mV).
3. V_{TT} is not applied directly to the device. It is the supply to which far end signal termination is made, and it is expected to be equal to MV_{REF}n with a min value of MV_{REF}n – 0.04 and a max value of MV_{REF}n + 0.04. V_{TT} should track variations in the DC level of MVREFn.
4. The voltage regulator for $MV_{REF}n$ must meet the specifications stated in Table 23.
5. Input capacitance load for DQ, DQS, and $\overline{DQS}$ are available in the IBIS models.
6. Output leakage is measured with all outputs disabled, 0 V ≤ V_{OUT} ≤ GV_{DD}.
7. Refer to the IBIS model for the complete output IV curve characteristics.
8. I_{OH} and I_{OL} are measured at GV_{DD} = 1.283 V

This table provides the DDR controller interface capacitance for DDR3 and DDR3L.

Table 22. DDR3 and DDR3L SDRAM Capacitance

For recommended operating conditions, see Table 3.

Parameter	Symbol	Min	Max	Unit	Note
Input/output capacitance: DQ, DQS, $\overline{DQS}$	C_{IO}	6	8	pF	1, 2
Delta input/output capacitance: DQ, DQS, $\overline{DQS}$	C_{DIO}	—	0.5	pF	1, 2

Note:

1. This parameter is sampled. GV_{DD} = 1.5 V ± 0.075 V (for DDR3), f = 1 MHz, T_A = 25 °C, V_{OUT} = GV_{DD} ÷ 2, V_{OUT} (peak-to-peak) = 0.150 V.
2. This parameter is sampled. GV_{DD} = 1.35 V – 0.067 V ÷ + 0.100 V (for DDR3L), f = 1 MHz, T_A = 25 °C, V_{OUT} = GV_{DD} ÷ 2, V_{OUT} (peak-to-peak) = 0.167 V.

This table provides the current draw characteristics for MVREF*n*.

Table 23. Current Draw Characteristics for MVREF*n*

For recommended operating conditions, see Table 3.

Parameter	Symbol	Min	Max	Unit	Note
Current draw for DDR3 SDRAM for MVREF*n*	MVREF*n*	—	500	μA	—
Current draw for DDR3L SDRAM for MVREF*n*	MVREF*n*	—	500	μA	—

2.9.2 DDR3 and DDR3L SDRAM Interface AC Timing Specifications

This section provides the AC timing specifications for the DDR SDRAM controller interface. The DDR controller supports DDR3 and DDR3L memories. Note that the required GV_{DD}(typ) voltage is 1.5 V when interfacing to DDR3 SDRAM and the required GV_{DD}(typ) voltage is 1.35 V when interfacing to DDR3L SDRAM.

This figure shows the DDR3 and DDR3L SDRAM interface output timing for the MCK to MDQS skew measurement (t_{DDKHMH}).

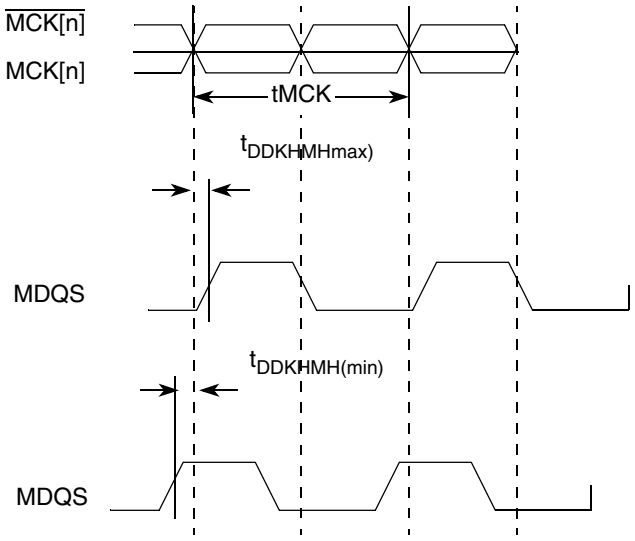


Figure 10. t_{DDKHMH} Timing Diagram

This figure shows the DDR3 and DDR3L SDRAM output timing diagram.

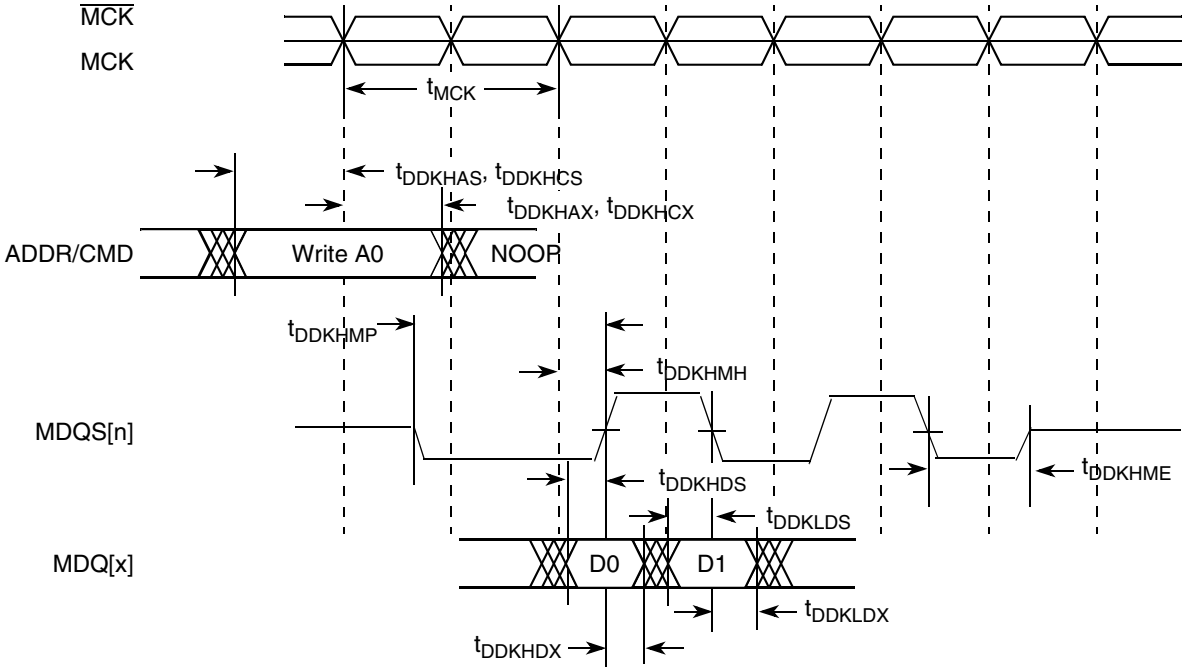


Figure 11. DDR3 and DDR3L Output Timing Diagram

This figure provides the AC test load for the DDR3 and DDR3L controller bus.

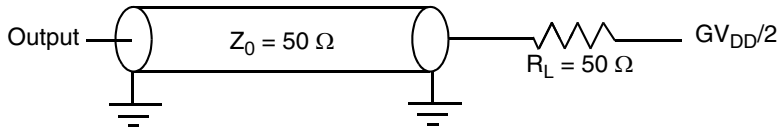


Figure 12. DDR3 and DDR3L Controller Bus AC Test Load

2.9.2.3 DDR3 and DDR3L SDRAM Differential Timing Specifications

This section describes the DC and AC differential timing specifications for the DDR3 and DDR3L SDRAM controller interface. This figure shows the differential timing specification.

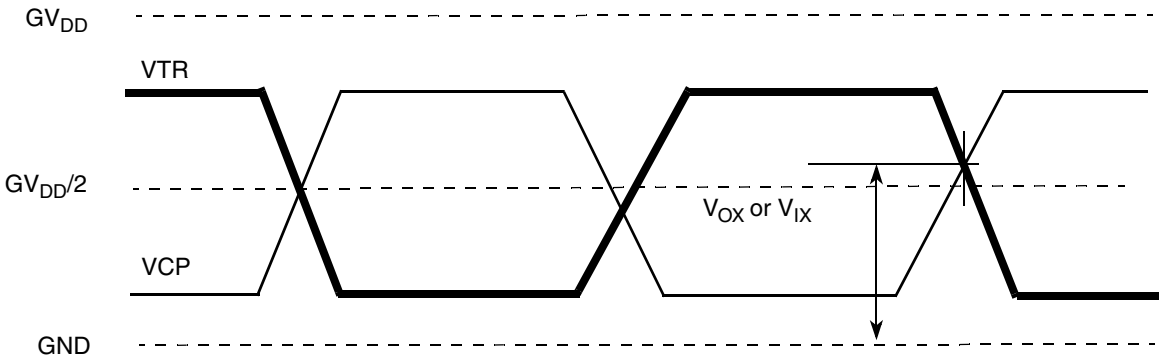


Figure 13. DDR3 and DDR3L SDRAM Differential Timing Specifications

NOTE

VTR specifies the true input signal (such as MCK or MDQS) and VCP is the complementary input signal (such as $\overline{\text{MCK}}$ or $\overline{\text{MDQS}}$).

This table provides the DDR3 differential specifications for the differential signals MDQS/$\overline{\text{MDQS}}$ and MCK/$\overline{\text{MCK}}$.

Table 28. DDR3 SDRAM Differential Electrical Characteristics[1]

Parameter	Symbol	Min	Max	Unit	Note
Input AC Differential Cross-Point Voltage	V_{IXAC}	$0.5 \times GV_{DD} - 0.150$	$0.5 \times GV_{DD} + 0.150$	V	—
Output AC Differential Cross-Point Voltage	V_{OXAC}	$0.5 \times GV_{DD} - 0.115$	$0.5 \times GV_{DD} + 0.115$	V	—

Note:
1. I/O drivers are calibrated before making measurements.

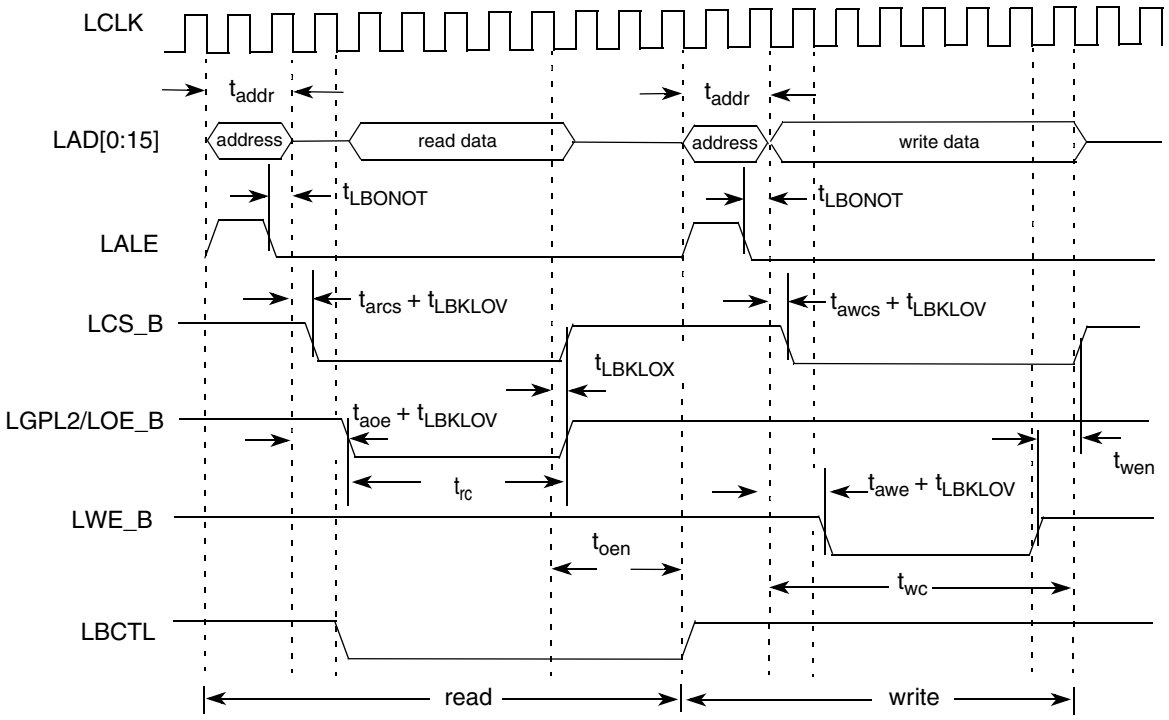
This table provides the DDR3L differential specifications for the differential signals MDQS/$\overline{\text{MDQS}}$ and MCK/$\overline{\text{MCK}}$.

Table 29. DDR3L SDRAM Differential Electrical Characteristics[1]

Parameter	Symbol	Min	Max	Unit	Note
Input AC differential cross-point voltage	V_{IXAC}	$0.5 \times GV_{DD} - 0.135$	$0.5 \times GV_{DD} + 0.135$	V	—
Output AC differential cross-point voltage	V_{OXAC}	$0.5 \times GV_{DD} - 0.105$	$0.5 \times GV_{DD} + 0.105$	V	—

Note:
1. I/O drivers are calibrated before making measurements.

This figure shows how the AC timing diagram applies to GPCM. The same principle applies to UPM and FCM.



1 t_{addr} is programmable and determined by LCRR[EADC] and ORx[EAD].

2 t_{arcs}, t_{awcs}, t_{aoe}, t_{rc}, t_{oen}, t_{awe}, t_{wc}, t_{wen} are determined by ORx. See the chip reference manual.

Figure 22. GPCM Output Timing Diagram

2.15 Enhanced Secure Digital Host Controller (eSDHC)

This section describes the DC and AC electrical specifications for the eSDHC interface.

2.15.1 eSDHC DC Electrical Characteristics

This table provides the eSDHC electrical characteristics.

Table 50. eSDHC Interface DC Electrical Characteristics

For recommended operating conditions, see Table 3.

Characteristic	Symbol	Condition	Min	Max	Unit	Note
Input high voltage	V_{IH}	—	$0.625 \times CV_{DD}$	—	V	1
Input low voltage	V_{IL}	—	—	$0.25 \times CV_{DD}$	V	1
Input/output leakage current	I_{IN}/I_{OZ}	—	–50	50	μA	—
Output high voltage	V_{OH}	I_{OH} = –100 μA at CV_{DD} min	$0.75 \times CV_{DD}$	—	V	—

The long run transmitter specifications use larger voltage swings that are capable of driving signals across backplanes. This allows a user to drive signals across two connectors and a backplane. The specifications allow a distance of at least 50 cm at all baud rates.

All unit intervals are specified with a tolerance of ±100 ppm. The worst case frequency difference between any transmit and receive clock is 200 ppm.

To ensure interoperability between drivers and receivers of different vendors and technologies, AC coupling at the receiver input must be used.

2.20.5.1 Signal Definitions

This section defines the terms used in the description and specification of the differential signals used by the LP-Serial links. This figure shows how the signals are defined. The figures show waveforms for either a transmitter output (TD and $\overline{\text{TD}}$) or a receiver input (RD and $\overline{\text{RD}}$). Each signal swings between A volts and B volts where A > B. Using these waveforms, the definitions are as follows:

- The transmitter output signals and the receiver input signals—TD, $\overline{\text{TD}}$, RD, and $\overline{\text{RD}}$—each have a peak-to-peak swing of A – B volts.
- The differential output signal of the transmitter, V_{OD}, is defined as $V_{TD} - V_{\overline{TD}}$
- The differential input signal of the receiver, V_{ID}, is defined as $V_{RD} - V_{\overline{RD}}$
- The differential output signal of the transmitter and the differential input signal of the receiver each range from A – B to –(A – B) volts
- The peak value of the differential transmitter output signal and the differential receiver input signal is A – B volts.
- The peak-to-peak value of the differential transmitter output signal and the differential receiver input signal is 2 × (A – B) volts.

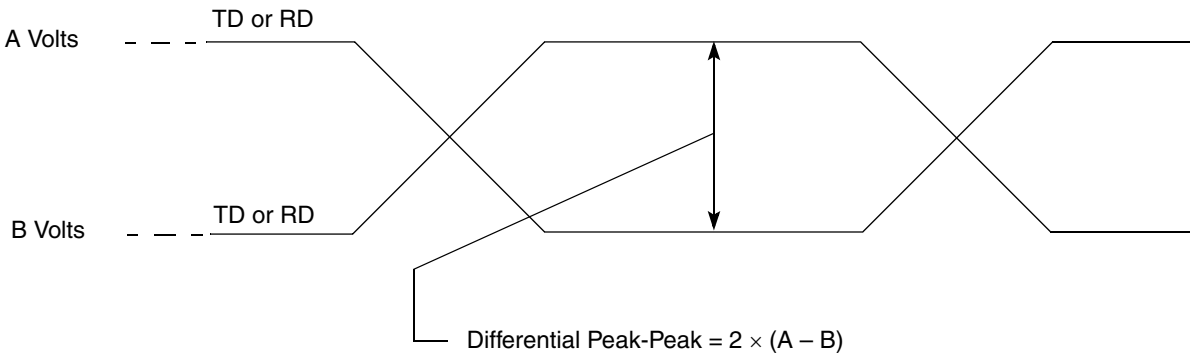


Figure 41. Differential Peak-Peak Voltage of Transmitter or Receiver

To illustrate these definitions using real values, consider the case of a CML (current mode logic) transmitter that has a common mode voltage of 2.25 V, and each of its outputs, TD and $\overline{\text{TD}}$, has a swing that goes between 2.5 V and 2.0 V. Using these values, the peak-to-peak voltage swing of the signals TD and $\overline{\text{TD}}$ is 500 mV p-p. The differential output signal ranges between 500 mV and –500 mV. The peak differential voltage is 500 mV. The peak-to-peak differential voltage is 1000 mV p-p.

2.20.5.2 Equalization

With the use of high-speed serial links, the interconnect media causes degradation of the signal at the receiver and produces effects such as inter-symbol interference (ISI) or data-dependent jitter. This loss can be large enough to degrade the eye opening at the receiver beyond what is allowed in the specification. To negate a portion of these effects, equalization can be used. The most common equalization techniques that can be used are as follows:

- Pre-emphasis on the transmitter
- A passive high-pass filter network placed at the receiver, often referred to as passive equalization.

- The use of active circuits in the receiver, often referred to as adaptive equalization.

2.20.5.3 Serial RapidIO Clocking Requirements for SD_REF_CLK*n* and SD_REF_CLK*n*

SerDes bank 1 (SD_REF_CLK1 and $\overline{\text{SD\_REF\_CLK1}}$) may be used for various SerDes Serial RapidIO configurations based on the RCW configuration field SRDS_PRTCL. Serial RapidIO is not supported on SerDes banks 2.

For more information on these specifications, see Section 2.20.2, "SerDes Reference Clocks."

2.20.5.4 DC Requirements for Serial RapidIO

This section explains the DC requirements for the Serial RapidIO interface.

2.20.5.4.1 DC Serial RapidIO Timing Transmitter Specifications

LP-Serial transmitter electrical and timing specifications are stated in the text and tables of this section.

The differential return loss, S11, of the transmitter in each case is better than the following:

- –10 dB for (Baud Frequency) ÷ 10 < Freq(f) < 625 MHz
- –10 dB + 10log(f ÷ 625 MHz) dB for 625 MHz ≤ Freq(f) ≤ Baud Frequency

The reference impedance for the differential return loss measurements is 100-Ω resistive. Differential return loss includes contributions from on-chip circuitry, chip packaging, and any off-chip components related to the driver. The output impedance requirement applies to all valid output levels.

It is recommended that the 20%–80% rise/fall time of the transmitter, as measured at the transmitter output, have a minimum value 60 ps in each case.

It is recommended that the timing skew at the output of an LP-Serial transmitter between the two signals that comprise a differential pair not exceed 20 ps at 2.50 GBaud and 15 ps at 3.125 GBaud and XX ps at 5 GBaud.

This table defines the transmitter DC specifications for Serial RapidIO operating at XV_{DD} = 1.5 V or 1.8 V.

Table 70. Serial RapidIO Transmitter DC Timing Specifications—2.5 GBaud, 3.125 GBaud, 5 GBaud

For recommended operating conditions, see Table 3.

Parameter	Symbol	Min	Typ	Max	Unit	Note
Output voltage	V_O	–0.40	—	2.30	V	1
Long-run differential output voltage	V_{DIFFPP}	800	—	1600	mV p-p	—
Short-run differential output voltage	V_{DIFFPP}	500	—	1000	mV p-p	—

Note:
1. Voltage relative to COMMON of either signal comprising a differential pair.

2.20.5.4.2 DC Serial RapidIO Receiver Specifications

LP-Serial receiver electrical and timing specifications are stated in the text and tables of this section.

Receiver input impedance results in a differential return loss better than 10 dB and a common mode return loss better than 6 dB from 100 MHz to (0.8) × (Baud Frequency). This includes contributions from on-chip circuitry, the chip package, and any off-chip components related to the receiver. AC coupling components are included in this requirement. The reference impedance for return loss measurements is 100-Ω resistive for differential return loss and 25-Ω resistive for common mode.

Table 83. Gen1i/1.5 G Transmitter (Tx) AC Specifications (continued)

For recommended operating conditions, see Table 3.

Parameter	Symbol	Min	Typ	Max	Unit	Note

Note:
1. Measured at Tx output pins peak to peak phase variation, random data pattern

This table provides the differential transmitter output AC characteristics for the SATA interface at Gen2i or 3.0 Gbits/s transmission. The AC timing specifications do not include RefClk jitter.

Table 84. Gen 2i/3 G Transmitter (Tx) AC Specifications

For recommended operating conditions, see Table 3.

Parameter	Symbol	Min	Typ	Max	Unit	Note
Channel speed	t_{CH_SPEED}	—	3.0	—	Gbps	—
Unit Interval	T_{UI}	333.2167	333.3333	335.1167	ps	—
Total jitter $f_{C3dB} = f_{BAUD} \div 10$	$U_{SATA\_TXTJfB/10}$	—	—	0.3	UI p-p	1
Total jitter $f_{C3dB} = f_{BAUD} \div 500$	$U_{SATA\_TXTJfB/500}$	—	—	0.37	UI p-p	1
Total jitter $f_{C3dB} = f_{BAUD} \div 1667$	$U_{SATA\_TXTJfB/1667}$	—	—	0.55	UI p-p	1
Deterministic jitter, $f_{C3dB} = f_{BAUD} \div 10$	$U_{SATA\_TXDJfB/10}$	—	—	0.17	UI p-p	1
Deterministic jitter, $f_{C3dB} = f_{BAUD} \div 500$	$U_{SATA\_TXDJfB/500}$	—	—	0.19	UI p-p	1
Deterministic jitter, $f_{C3dB} = f_{BAUD} \div 1667$	$U_{SATA\_TXDJfB/1667}$	—	—	0.35	UI p-p	1

Note:
1. Measured at Tx output pins peak-to-peak phase variation, random data pattern

2.20.7.4 AC Differential Receiver Input Characteristics

This table provides the Gen1i or 1.5 Gbits/s differential receiver input AC characteristics for the SATA interface. The AC timing specifications do not include RefClk jitter.

Table 85. Gen 1i/1.5G Receiver (Rx) AC Specifications

For recommended operating conditions, see Table 3.

Parameter	Symbol	Min	Typical	Max	Unit	Note
Unit Interval	T_{UI}	666.4333	666.6667	670.2333	ps	—
Total jitter data-data 5 UI	$U_{SATA\_TXTJ5UI}$	—	—	0.43	UI p-p	1
Total jitter, data-data 250 UI	$U_{SATA\_TXTJ250UI}$	—	—	0.60	UI p-p	1
Deterministic jitter, data-data 5 UI	$U_{SATA\_TXDJ5UI}$	—	—	0.25	UI p-p	1
Deterministic jitter, data-data 250 UI	$U_{SATA\_TXDJ250UI}$	—	—	0.35	UI p-p	1

Note:
1. Measured at receiver.

This table provides the differential receiver input AC characteristics for the SATA interface at Gen2i or 3.0 Gbits/s transmission. The AC timing specifications do not include RefClk jitter.

Table 86. Gen 2i/3G Receiver (Rx) AC Specifications

For recommended operating conditions, see Table 3.

Parameter	Symbol	Min	Typical	Max	Unit	Note
Unit Interval	T_{UI}	333.2167	333.3333	335.1167	ps	—
Total jitter $f_{C3dB} = f_{BAUD} \div 10$	$U_{SATA\_TXTJfB/10}$	—	—	0.46	UI p-p	1
Total jitter $f_{C3dB} = f_{BAUD} \div 500$	$U_{SATA\_TXTJfB/500}$	—	—	0.60	UI p-p	1
Total jitter $f_{C3dB} = f_{BAUD} \div 1667$	$U_{SATA\_TXTJfB/1667}$	—	—	0.65	UI p-p	1
Deterministic jitter, $f_{C3dB} = f_{BAUD} \div 10$	$U_{SATA\_TXDJfB/10}$	—	—	0.35	UI p-p	1
Deterministic jitter, $f_{C3dB} = f_{BAUD} \div 500$	$U_{SATA\_TXDJfB/500}$	—	—	0.42	UI p-p	1
Deterministic jitter, $f_{C3dB} = f_{BAUD} \div 1667$	$U_{SATA\_TXDJfB/1667}$	—	—	0.35	UI p-p	1

Note:
1. Measured at receiver.

2.20.8 SGMII Interface

Each SGMII port features a 4-wire AC-coupled serial link from the SerDes interface of the device, as shown in Figure 44, where C_{TX} is the external (on board) AC-coupled capacitor. Each output pin of the SerDes transmitter differential pair features 50-Ω output impedance. Each input of the SerDes receiver differential pair features 50-Ω on-die termination to XGND. The reference circuit of the SerDes transmitter and receiver is shown in Figure 39.

2.20.8.0.1 SGMII Clocking Requirements for SD_REF_CLK*n* and $\overline{\text{SD\_REF\_CLK}n}$

When operating in SGMII mode, the EC_GTX_CLK125 clock is not required for this port. Instead, a SerDes reference clock is required on SD_REF_CLK[1:2] and $\overline{\text{SD\_REF\_CLK}[1:2]}$ pins. SerDes banks 1–2 may be used for SerDes SGMII configurations based on the RCW Configuration field SRDS_PRTCL.

For more information on these specifications, see Section 2.20.2, “SerDes Reference Clocks.”

2.20.8.1 SGMII DC Electrical Characteristics

This section discusses the electrical characteristics for the SGMII interface.

2.20.8.1.1 SGMII Transmit DC Timing Specifications

This table describe the SGMII SerDes transmitter and receiver AC-coupled DC electrical characteristics for 1.25 GBaud. Transmitter DC characteristics are measured at the transmitter outputs (SD_TX*n* and $\overline{\text{SD\_TX}n}$) as shown in Figure 45.

Table 87. SGMII DC Transmitter Electrical Characteristics (XV_{DD} = 1.5 V or 1.8 V)

For recommended operating conditions, see Table 3.

Parameter	Symbol	Min	Typ	Max	Unit	Note
Output high voltage	V_{OH}	—	—	1.5 x $\lvert V_{OD}\rvert_{-max}$	mV	1
Output low voltage	V_{OL}	$\lvert V_{OD}\rvert_{-min}/2$	—	—	mV	1

3.1.2 Platform to SYSCLK PLL Ratio

This table shows the allowed platform clock-to-SYSCLK ratios.

The chip platform clock frequency is always below 666 MHz frequencies; set the RCW configuration field SYS_PLL_CFG = 0b01.

Table 94. Platform to SYSCLK PLL Ratios

Binary Value of SYS_PLL_RAT	Platform:SYSCLK Ratio
0_0100	4:1
0_0101	5:1
0_0110	6:1
0_0111	7:1
0_1000	8:1
0_1001	9:1
All Others	Reserved

3.1.3 e500mc Core Cluster to SYSCLK PLL Ratio

The clock ratio between SYSCLK and each of the two core cluster PLLs is determined at power up by the binary value of the RCW field CCn_PLL_RAT. This table describes the supported ratios. Note that a core cluster PLL frequency targeting 1 GHz and above must set RCW field CCn_PLL_CFG = 0b00 for frequency targeting below 1 GHz set CCn_PLL_CFG = 0b01.

This table lists the supported Core Cluster to SYSCLK ratios.

Table 95. e500mc Core Cluster PLL to SYSCLK Ratios

Binary Value of CCn_PLL_RAT	Core Cluster:SYSCLK Ratio
0_1000	8:1
0_1001	9:1
0_1010	10:1
0_1011	11:1
0_1100	12:1
0_1101	13:1
0_1110	14:1
0_1111	15:1
1_0000	16:1
1_0001	17:1
1_0010	18:1
All Others	Reserved

See Section 19.4 “LP-Serial Signal Descriptions,” in the chip reference manual for Serial RapidIO interface width and frequency details.

3.1.7 SerDes PLL Ratio

The clock ratio between each of the three SerDes PLLs and their respective externally supplied SD_REF_CLK*n*/$\overline{\text{SD\_REF\_CLK}n}$ inputs is determined by the binary value of the RCW Configuration field SRDS_RATIO_B*n* as shown in this table. Furthermore, each SerDes lane grouping can be run at a SerDes PLL frequency divider determined by the binary value of the RCW field SRDS_DIV_B*n* as shown in Table 103.

This table lists the supported SerDes PLL Bank *n* to SD_REF_CLK*n* ratios.

Table 101. SerDes PLL Bank *n* to SD_REF_CLK*n* Ratios

Binary Value of SRDS_RATIO_B1	SRDS_PLL_*n*:SD_REF_CLK*n* Ratio	
	***n* = 1 (Bank)**	***n* = 2 (Bank 2)**
000	Reserved	Reserved
001	Reserved	20:1
010	25:1	25:1
011	40:1	40:1
100	50:1	50:1
101	Reserved	24:1
110	Reserved	30:1
All Others	Reserved	Reserved

These tables list the supported SerDes PLL dividers.

This table shows the PLL divider support for each pair of lanes on SerDes Bank 1.

Table 102. SerDes Bank 1 PLL Dividers

Binary Value of SRDS_DIV_B1[0:4]	SerDes Bank 1 PLL Divider
0b0	Divide by 1 off Bank 1 PLL
0b1	Divide by 2 off Bank 1 PLL

Note: 1 bit (of 5 total SRDS_DIV_B1 bits) controls each pair of lanes.

This table shows the PLL dividers supported for each 4-lane for SerDes Banks 2.

Table 103. SerDes Banks 2 PLL Dividers

Binary Value of SRDS_DIV_B2	SerDes Bank *2* PLL Divider
0b0	Divide by 1 off Bank *2* PLL
0b1	Divide by 2 off Bank *2* PLL

Note: 1 bit controls all four lanes of bank 2.

3.1.8 Frame Manager (FMan) Clock Select

The Frame Managers (FM) can each be synchronous to the platform.

This table describes the clocking options that may be applied to each FM. The clock selection is determined by the binary value of the RCW clocking configuration fields FM_CLK_SEL.

Table 104. Frame Manager Clock Select

Binary Value of FM_CLK_SEL	FM Frequency
0b0	Platform Clock Frequency /2
0b1	Core Cluster 2 Frequency /2[1]

Notes:

1 For asynchronous mode, max frequency, see Table 93.

3.2 Supply Power Default Setting

The device is capable of supporting multiple power supply levels on its I/O supplies. The I/O voltage select inputs, shown in Table 105, properly configure the receivers and drivers of the I/Os associated with the BVDD, CVDD, and LVDD power planes, respectively.

WARNING

Incorrect voltage select settings can lead to irreversible device damage.

3.6.3 Guidelines for High-Speed Interface Termination

This section provides the guidelines for when the SerDes interface is either entirely unused or partly unused.

3.6.3.1 SerDes Interface Entirely Unused

If the high-speed SerDes interface is not used at all, the unused pin must be terminated as described in this section.

The following pins must be left unconnected:

- SD_TX[7:2], SD_TX[13:10]
- $\overline{\text{SD\_TX}}$[7:2], $\overline{\text{SD\_TX}}$[13:10]
- SD_IMP_CAL_RX
- SD_IMP_CAL_TX

The following pins must be connected to SGND:

- SD_RX[7:2], SD_RX[13:10]
- $\overline{\text{SD\_RX}}$[13:10], $\overline{\text{SD\_RX}}$[13:10]
- SD_REF_CLK1, SD_REF_CLK2
- $\overline{\text{SD\_REF\_CLK1}}$, $\overline{\text{SD\_REF\_CLK2}}$

In the RCW configuration fields SRDS_LPD_B1 and SRDS_LPD_B2, all bits must be set to power down all the lanes in each bank.

RCW configuration field SRDS_EN may be cleared to power down the SerDes block for power saving. Setting RCW[SRDS_EN] = 0 power-downs the PLLs of both banks.

Additionally, software may configure SRDSB*n*RSTCTL[SDRD] = 1 for the unused banks to power down the SerDes bank PLLs to save power.

Note that both SV_{DD} and XV_{DD} must remain powered.

3.6.3.2 SerDes Interface Partly Unused

If only part of the high speed SerDes interface pins are used, the remaining high-speed serial I/O pins must be terminated as described in this section.

The following unused pins must be left unconnected:

- SD_TX[*n*]
- $\overline{\text{SD\_TX}}$[*n*]

The following unused pins must be connected to SGND:

- SD_RX[*n*]
- $\overline{\text{SD\_RX}}$[*n*]
- SD_REF_CLK1, $\overline{\text{SD\_REF\_CLK1}}$ (If entire SerDes bank 1 unused)
- SD_REF_CLK2, $\overline{\text{SD\_REF\_CLK2}}$ (If entire SerDes bank 2 unused)

In the RCW configuration field for each bank SRDS_LPD_B*n* with unused lanes, the respective bit for each unused lane must be set to power down the lane.

3.6.4 USB Controller Connections

This section details the hardware connections required for the USB controllers.

and thermal interface material. The recommended attachment method to the heat sink is illustrated in Figure 61. The heat sink must be attached to the printed-circuit board with the spring force centered over the die. This spring force should not exceed 10 pounds force (45 Newton).

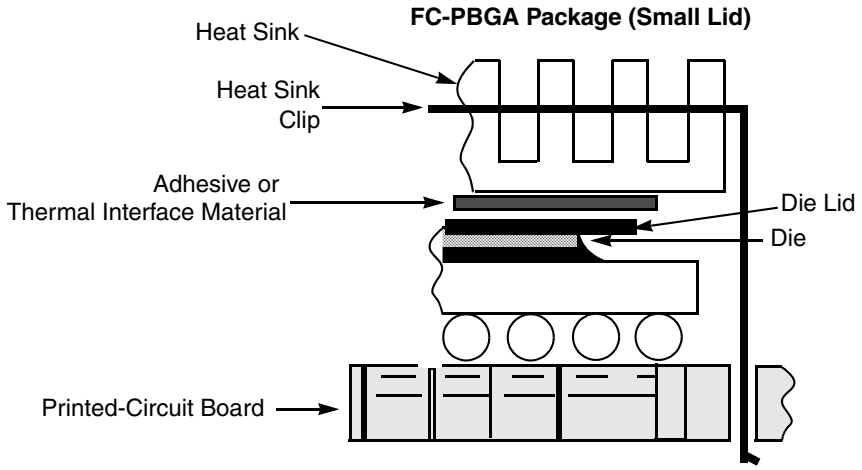


Figure 61. Package Exploded Cross-Sectional View—FC-PBGA (w/ Lid) Package

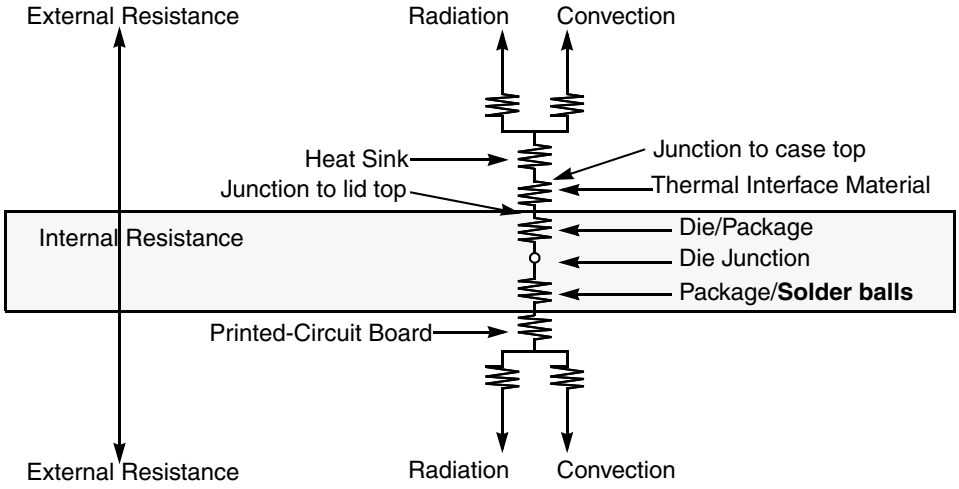
The system board designer can choose between several types of heat sinks to place on the device. There are several commercially-available thermal interfaces to choose from in the industry. Ultimately, the final selection of an appropriate heat sink depends on many factors, such as thermal performance at a given air velocity, spatial volume, mass, attachment method, assembly, and cost.

3.8.1 Internal Package Conduction Resistance

For the package, the intrinsic internal conduction thermal resistance paths are as follows:

- The die junction-to-case thermal resistance
- The die junction-to-lid-top thermal resistance
- The die junction-to-board thermal resistance

Figure 62 depicts the primary heat transfer path for a package with an attached heat sink mounted to a printed-circuit board.

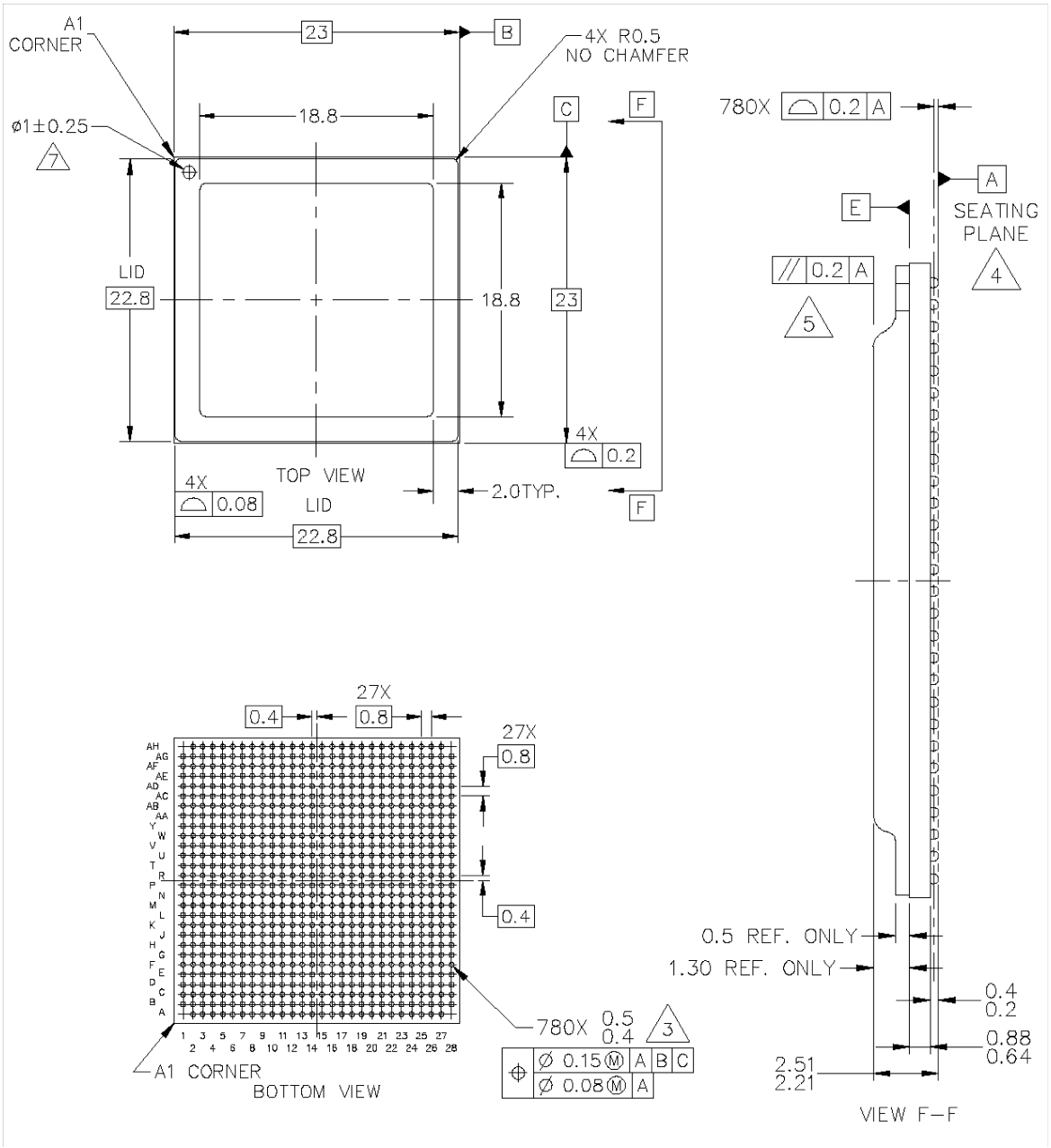


(Note the internal versus external package resistance)

Figure 62. Package with Heat Sink Mounted to a Printed-Circuit Board

4.2 Mechanical Dimensions of the FC-PBGA

This figure shows the mechanical dimensions and bottom surface nomenclature of the device.



Notes:

1. All dimensions are in millimeters.
2. Dimensions and tolerances per ASME Y14.5M-1994.
3. Maximum solder ball diameter measured parallel to datum A.
4. Datum A, the seating plane, is determined by the spherical crowns of the solder balls.
5. Parallelism measurement excludes any effect of mark on top surface of package.
6. All dimensions are symmetric across the package center lines unless dimensioned otherwise.
7. Pin 1 thru hole is centered within foot area.

Figure 63. Mechanical Dimensions of the FC-PBGA with Full Lid